

TOSHIBA TRANSISTOR SILICON PNP EPITAXIAL TYPE (PCT PROCESS)

2SA1425

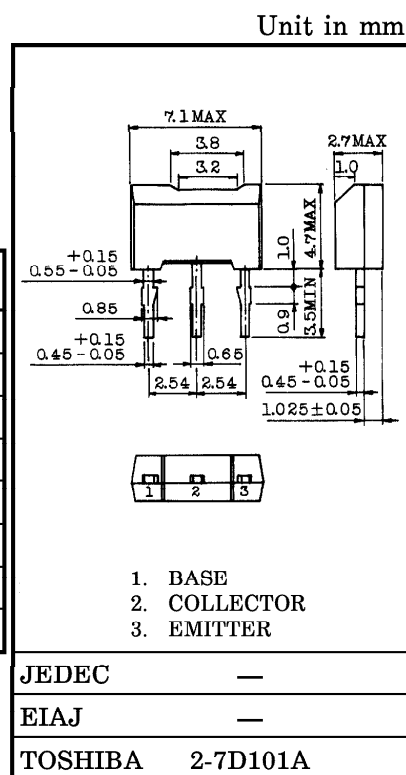
POWER AMPLIFIER APPLICATIONS.

DRIVER STAGE AMPLIFIER APPLICATIONS.

- Complementary to 2SC3665.

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	-120	V
Collector-Emitter Voltage	V_{CEO}	-120	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current	I_C	-800	mA
Base Current	I_B	-80	mA
Collector Power Dissipation	P_C	1000	mW
Junction Temperature	T_j	150	$^{\circ}\text{C}$
Storage Temperature Range	T_{stg}	$-55\sim 150$	$^{\circ}\text{C}$



ELECTRICAL CHARACTERISTICS (Ta = 25°C)

Weight : 0.2g

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	$V_{CB} = -120V, I_E = 0$	—	—	-100	nA
Emitter Cut-off Current	I_{EBO}	$V_{EB} = -5V, I_C = 0$	—	—	-100	nA
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = -10mA, I_B = 0$	-120	—	—	V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E = -1mA, I_C = 0$	-5	—	—	V
DC Current Gain	h_{FE} (Note)	$V_{CE} = -5V, I_C = -100mA$	80	—	240	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = -500mA, I_B = -50mA$	—	—	-1.0	V
Base-Emitter Voltage	V_{BE}	$V_{CE} = -5V, I_C = -500mA$	—	—	-1.0	V
Transition Frequency	f_T	$V_{CE} = -5V, I_C = -100mA$	—	120	—	MHz
Collector Output Capacitance	C_{ob}	$V_{CB} = -10V, I_E = 0, f = 1MHz$	—	—	40	pF

Note : hFF Classification O : 80~160, Y : 120~240

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